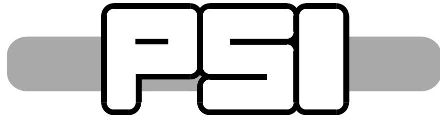

PICO

# SPTS Rapier DRIE system

## Responsible

Konstantins Jefimovs

## System Description

A dedicated etcher for Silicon deep reactive ion etching using Bosch or non-switch processes and for $SiO_2$ etching.

The mask materials are currently limited to photoresists and $SiO_2$. $Al_2O_3$ masks are under investigation.

Metals (neither as etching masks not as etching materials) are generally not allowed. Some exceptions can be made (for example, in case of small area samples on support wafers or as an etch stop) after detailed discussion with system responsible.

## Sample size:

Electrostatic clamps (ESC) and wafer edge protective (WEP) rings of three sizes are available: 100 mm, 150 mm and 200 mm and can be installed on demand.

## Gases available:

$SF_6$, $C_4F_8$, $O_2$, $N_2$, Ar

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